## Erratum: Spin depolarization of holes and lineshape of the Hanle effect in semiconductor nanostructures [Phys. Rev. B 80, 113301 (2009)]

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The main result of this paper is given by Eq. (3):

$$S_z = \frac{T_s}{\tau} S_{z0} \tilde{b}^{-2} \exp(\tilde{b}^{-2}) \operatorname{Ei}(\tilde{b}^{-2}) \equiv \frac{T_s}{\tau} S_{z0} A(\tilde{b})$$

and we have cited Ref. 1 as the reference for defining the standard function Ei(x). This *combination* is unfortunately incorrect. Keeping to the notation of Ref. 1, the correct expression should contain the relevant function  $E_1(x)$  instead of Ei(x), i.e.,

$$S_z = \frac{T_s}{\tau} S_{z0} \tilde{b}^{-2} \exp(\tilde{b}^{-2}) E_1(\tilde{b}^{-2}) \equiv \frac{T_s}{\tau} S_{z0} A(\tilde{b}).$$

To avoid further ambiguities, we quote here a series expansion for  $E_1(x)$ :

$$E_1(x) = -\gamma - \ln(x) - \sum_{n=1}^{\infty} (-1)^n \frac{x^n}{nn!} \quad (x > 0),$$

where  $\gamma \approx 0.577...$ 

The error was solely in the notation. Neither the calculation results nor any conclusions were affected.

<sup>&</sup>lt;sup>1</sup>M. Abramowitz and I. A. Stegun, *Handbook of Mathematical Functions* (Dover, New York, 1964).